

**Notice of References Cited**

Application/Control No.

09/582,630

Applicant(s)/Patent Under  
Reexamination  
DI CIOCCIO, LEA DI

Examiner

Caridad M. Everhart

Art Unit

2825

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification	
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	K	US-				
	L	US-				
	M	US-				

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**NON-PATENT DOCUMENTS**

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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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